

Please rewrite the following claims:

1(amended). A gaseous composition at a temperature below about 200°C at atmospheric pressure, adapted to deposit at least a first layer of tin oxide and silicon oxide onto glass at a rate of deposition greater than about 350Å/sec. [at a temperature below about 200°C, at atmospheric pressure,] wherein the composition comprises a precursor of tin oxide, a precursor of silicon oxide of formula R_mO_nSi_p, where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl, an accelerator selected from the group consisting of organic phosphites, organic borates and water, and mixtures thereof, and a source of oxygen.

a 2(amended). The gaseous composition of claim 1, adapted to deposit at least a first layer comprising tin oxide and silicon oxide onto [wherein the substrate is] transparent flat glass at a temperature of from 450 to about 650°C.

3(amended). The gaseous composition of claim 1, adapted to deposit at least a first layer comprising tin oxide and silicon oxide onto transparent flat glass to produce [producing] a glass article having essentially no reflected color in daylight.

4(amended). The gaseous composition of claim 1 adapted to continuously deposit at least a first layer of tin oxide and silicon oxide onto a [wherein the] continuously moving transparent flat glass substrate [is moving and the deposition is continuous].

A2 6(amended). The composition of claim 1 wherein the [accelerator is triethyl phosphite] organic phosphite and organic borate accelerants have the formula (R'O)₃P and (R'O)₃B where R' is independently chosen from straight, cyclic or branched-chain alkyl or alkenyl of from one

a 2 to about six carbons; phenyl, substituted phenyl, or R''' CH₂CH₂- where R''' is MeO₂C-, EtO₂C-, CH₃CO-, or HOOC-.

b 16 (amended). The gaseous composition of claim 1 adapted to deposit at least a first layer of tin oxide and silicon oxide onto glass [wherein the] at a rate of deposition greater than about 400Å/sec.

c 17 (amended). The gaseous composition of claim 1 adapted to deposit at least a first amorphous layer of tin oxide and silicon oxide onto glass [wherein the first layer is amorphous].

d 18 (amended). The gaseous composition of claim 1 adapted to deposit a plurality of layers comprising tin oxide and silicon oxide onto glass, the outermost layer of which is further adapted for deposit of at least a second layer [wherein the first layer comprises a plurality of layers and at least a second layer deposited on the first layer].

e 19 (amended). The composition of claim 18 adapted to deposit a plurality of layers comprising tin oxide and silicon oxide onto glass, the outermost layer of which is further adapted for deposit of a layer comprising tin oxide [wherein the second layer comprises a tin oxide].

f 20 (amended). The composition of claim 18 adapted to deposit a plurality of layers comprising tin oxide and silicon oxide onto glass, the outermost layer of which is further adapted for deposit of a layer comprising tin oxide and fluorine [wherein the second layer comprises a mixture of tin oxide and a fluorine compound].

g 21 (amended). The composition of claim [18] 1 adapted to deposit at least a first layer comprising tin oxide and silicon oxide onto glass, [wherein the first layer has] said first layer having a refractive index which changes continuously between the glass substrate and the [second] top of the layer.

21 24(amended) The composition of claim 18 wherein [the first layer is] said plurality of layers are deposited from a precursor mixture comprising monobutyltin trichloride, tetraethyl orthosilicate [in the presence of] and triethyl phosphite.

25 25(amended). A gaseous composition at a temperature below about 200°C at atmospheric pressure, adapted to deposit at least a first amorphous layer [of] comprising tin oxide and silicon oxide onto glass [at a temperature below about 200°C at atmospheric pressure by the method of depositing at least one amorphous layer] at a rate of deposition greater than about 400Å/sec., the layer having a controlled index of refraction, [by applying to the glass] wherein the composition comprises [a mixture of] a tin oxide precursor, a silicon oxide precursor of formula $R_mO_nSi_p$, where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl, and at least one accelerant chosen from the group consisting of boron and phosphorous esters and water.

a 4 *26* 26(amended). The gaseous composition of claim 25 adapted to continuously deposit at least a first layer comprising tin oxide and silicon oxide onto a continuously moving flat glass substrate at a temperature of from about 450 to about 650°C, and comprising [applied by continuous chemical-vapor deposition of a mixture of] monobutyltin trichloride, tetraethyl orthosilicate and an accelerant [onto a moving glass sheet, wherein the glass is at a temperature of from about 450 to about 650°C].

E [Please add the following new claims:]

a 5 25 27. A gaseous composition at a temperature below about 200°C and at atmospheric pressure, adapted to deposit at least a first layer comprising amorphous tin oxide and silicon

oxide onto glass at a temperature of from about 450 to 650°C at a rate of deposition greater than about 350Å/sec., wherein the composition comprises:

a tin oxide precursor of formula R_nSnX_{4-n} , where R is a straight, cyclic, or branched-chain alkyl, or alkenyl of from one to about six carbons; phenyl, substituted phenyl, or $R'CH_2CH_2^-$, where R' is MeO_2C- , EtO_2C- , CH_3CO- , or HO_2C- ; X is selected from the group consisting of halogen, acetate, perfluoroacetate, and their mixtures; and where n is 0, 1, or 2;

a silicon oxide precursor of formula $R_mO_nSi_p$, where m is from 3 to 8, n is from 1 to 4, p is from 1 to 4, and R is independently chosen from hydrogen and acyl, straight, cyclic, or branched-chain alkyl and substituted alkyl or alkenyl of from one to about six carbons, and phenyl or substituted phenyl;

one or more accelerants selected from the group consisting of water and organic phosphites and organic borates of formula $(R''O)_3P$ and $(R''O)_3B$ where R'' is independently chosen from straight, cyclic or branched-chain alkyl or alkenyl of from one to about six carbons; phenyl, substituted phenyl, or $R'''CH_2CH_2^-$, where R''' is MeO_2C- , EtO_2C- , CH_3CO- , or $HOOC-$; and

a source of oxygen.

26 28. A composition according to claim *21* in which the precursor of the tin oxide is an alkyltin halide, the precursor of the silicon oxide is tetraethylorthosilicate, diacetoxymethylbutoxysilane, ethyltriacetoxysilane, methyltriacetoxysilane, methyldiacetoxysilane, tetramethyldisiloxane, tetramethylcyclotetrasiloxane, dipinacoloxysilane, 1,1-dimethylsila-2-oxacyclohexane, tetrakis (1-methoxy-2-propoxy) silane, or triethoxysilane, and the accelerant comprises one or both of triethyl phosphite and triethyl borate.

27 *28* *29* A composition according to claim *28* in which the tin oxide precursor comprises monobutyltin trichloride, the silicon oxide precursor comprises tetraethyl orthosilicate and the accelerant comprises triethyl phosphite.

Status of the Claims

In the Office Action of September 20, 1994, the Examiner rejected claims 1-10, 14-23, 25 and 26 under 35 USC §112, first paragraph, as being broader than the disclosure and stated that the disclosure is enabling only for a silicon oxide precursor defined as in claim 11.

The Examiner rejected claims 2-4, 18-24 and 26 under 35 USC §112 fourth paragraph as being of improper dependent form because they define the intended use and do not further define the composition claims from which they depend.

The Examiner objected to claims 11-13 as being dependent on a rejected base claim.

The Examiner indicated that all claims would be allowable if rewritten to overcome the rejections under 35 USC §112.

Claims 1-10 and 14-26 stand rejected.

Claims 11-13 are objected to.

Claims 1-10, 12-21 and 24-29 are in the case.

REMARKS

By the foregoing amendment Applicants have modified the claims in order to more particularly point out and distinctly claim the invention. Entry of the amendment and reconsideration of the application in light thereof and in light of the following remarks are respectfully requested.

The amendments are fully supported by the specification and original claims, neither present nor include new matter and are entitled entry.